

[illegible][illegible]

S186 and S147

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	U	I	Inventor	Document	Issued	P	Title	Current	Current	Retrieval	S	C	P	S	Image	Def
1			TISCHLER, M	US 200100	2001	11	BULK SINGLE CRYSTAL GALLIUM NITRIDE A	428/34	257/E21.11							US 200100
2			Schetzina, J	US 604646	2000	4	Integrated heterostructures of group II	257/96	257/180							US 604646
3			Carter, Jr., C	US 521005	1993	14	High efficiency light emitting diodes fr	438/22	117/105							US 521005
4			Edmond, J	US 612060	2000	15	Double heterojunction light emitting di	117/89	117/104							US 612060
5			Tanaka, T	US 637759	2002	3	Semiconductor materials, methods for	372/45	257/52							US 637759
6			Kub, Franz	US 632879	2001	9	Single-crystal material on non-single-	117/04	117/815							US 632879
7			Redwing, Jo	US 587474	1999	31	High brightness electroluminescent d	257/77	257/103							US 587474
8			Tischler, M	US 567915	1997	10	Method of making a single crystals Ga	117/97	117/1							US 567915
9			Zhaleev, Tev	US 62652	2001	2	Methods of fabricating gallium nitride	438/50	257/180							US 62652
10			MOTOKI, KEN	US 200200	2002	16	GALLIUM NITRIDE SINGLE CRYSTAL SUBST	257/76	257/E21.11							US 20020